Abstracts

Study of self-heating effects in GaN HEMTs

S. Nuttinck, E. Gebara, J. Laskar and M. Harris. "Study of self-heating effects in GaN HEMTs." 2001 MTT-S International Microwave Symposium Digest 01.3 (2001 Vol. III [MWSYM]): 2151-2154 vol.3.

Pulsed RF and I-V characterizations are performed on power GaN HEMTs. These measurements are carried out at different temperatures for the first time to understand self-heating effects and to investigate the possibility of improving heat dissipation mechanisms. These measurements are the basis for robust large-signal models.

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